

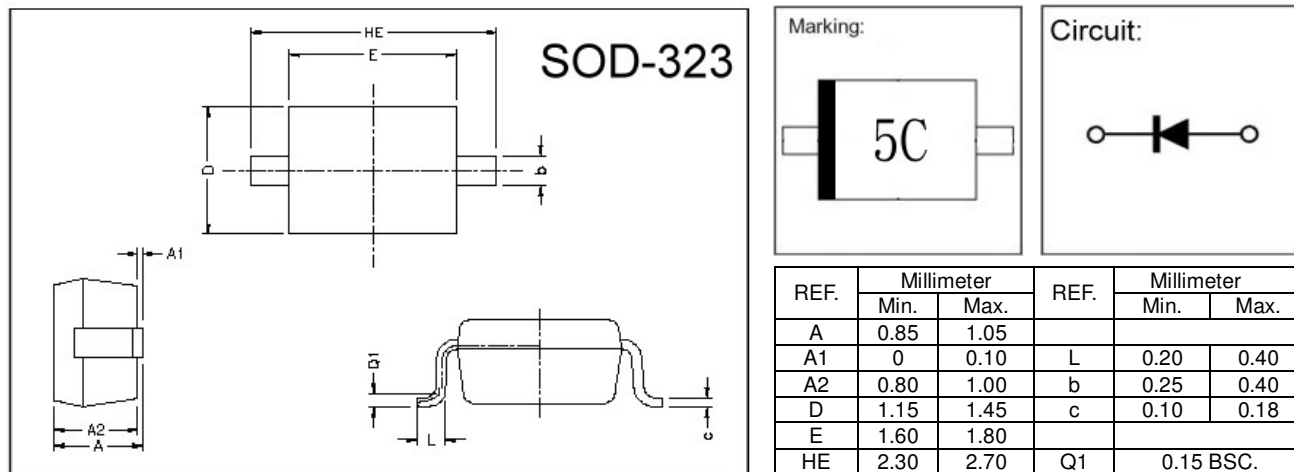
GD551SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 30V, CURRENT 0.5A

Description

The GD551SD is designed for low power rectification and high reliability.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Peak Repetitive Reverse Voltage	V _{RRM}	30	V
Maximum RMS Voltage	V _{RMS}	21	V
Maximum DC Blocking Voltage	V _{DC}	20	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	2.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	15	pF
Maximum Average Forward Rectified Current	I _o	0.5	A
Total Power Dissipation	PD	225	mW

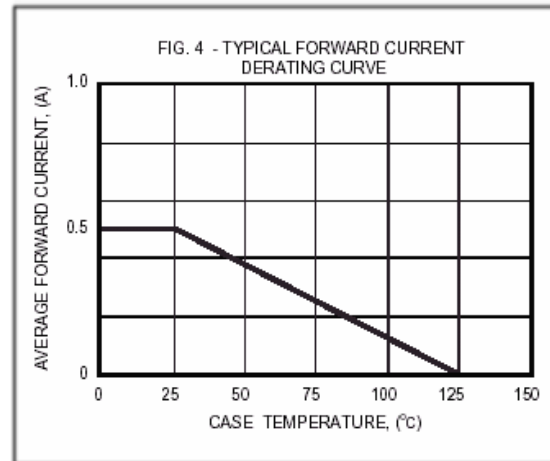
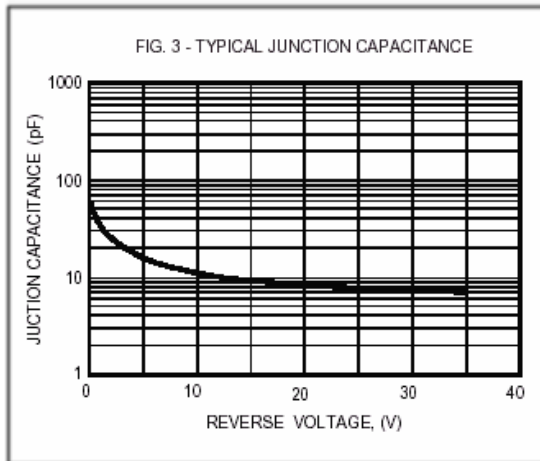
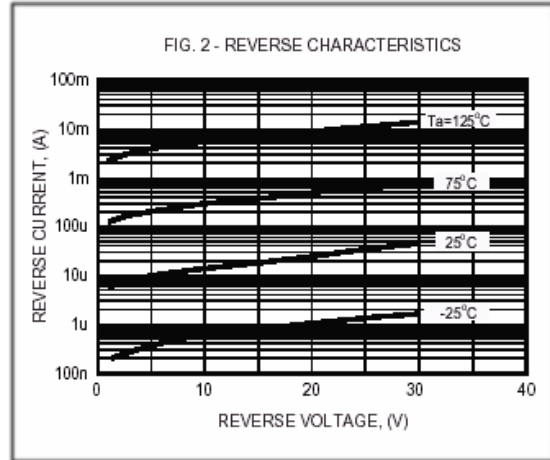
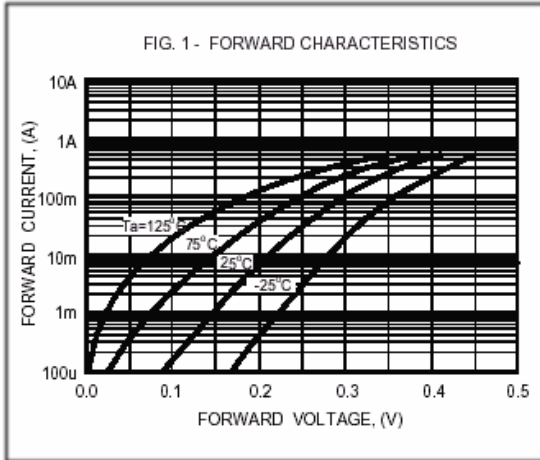
Characteristics at Ta = 25°C

Characteristics	Symbol	Max	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _{F(1)}	0.47	V	I _F = 500mA
Maximum Instantaneous Forward Voltage	V _{F(2)}	0.36	V	I _F = 100mA
Maximum Average Reverse Current	I _R	100	uA	V _R = 20V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volt.

2. ESD sensitive product handling required.

Characteristics Curve



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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165